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P. Polovodov, Sophie Eliet, O. Haenssler, Gilles Dambrine, Kamel Haddadi, et al.. A near-field scanning microwave microscope in a scanning electron microscope: design and challenges. 21st International Scanning Probe Microscopy, May 2019, Louvain la Neuve, France. hal-02278736

HAL Id: hal-02278736

<https://hal.science/hal-02278736>

Submitted on 4 Sep 2019

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A near-field scanning microwave microscope in a scanning electron microscope: design and challenges.

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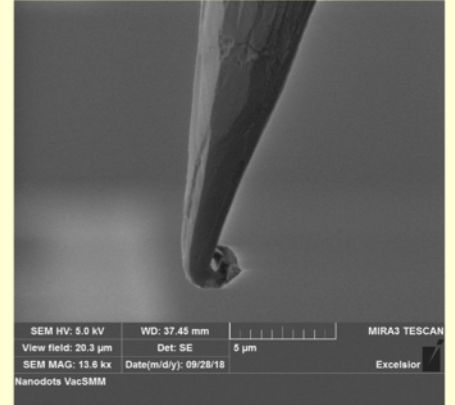
Multimodal Atomic Force Microscopy, Microwaves, and Scanning Electron Microscopy

Context and objectives

- SMM combines an AFM with microwaves. It allows the nanoscale electrical characterization of material properties.
- However the AFM probe tip can not be monitored during the experiment => possible shape evolution that impacts the effective electric contact area.
- Water forms a meniscus at the tip - sample interface => uncontrolled parasitic capacitance.

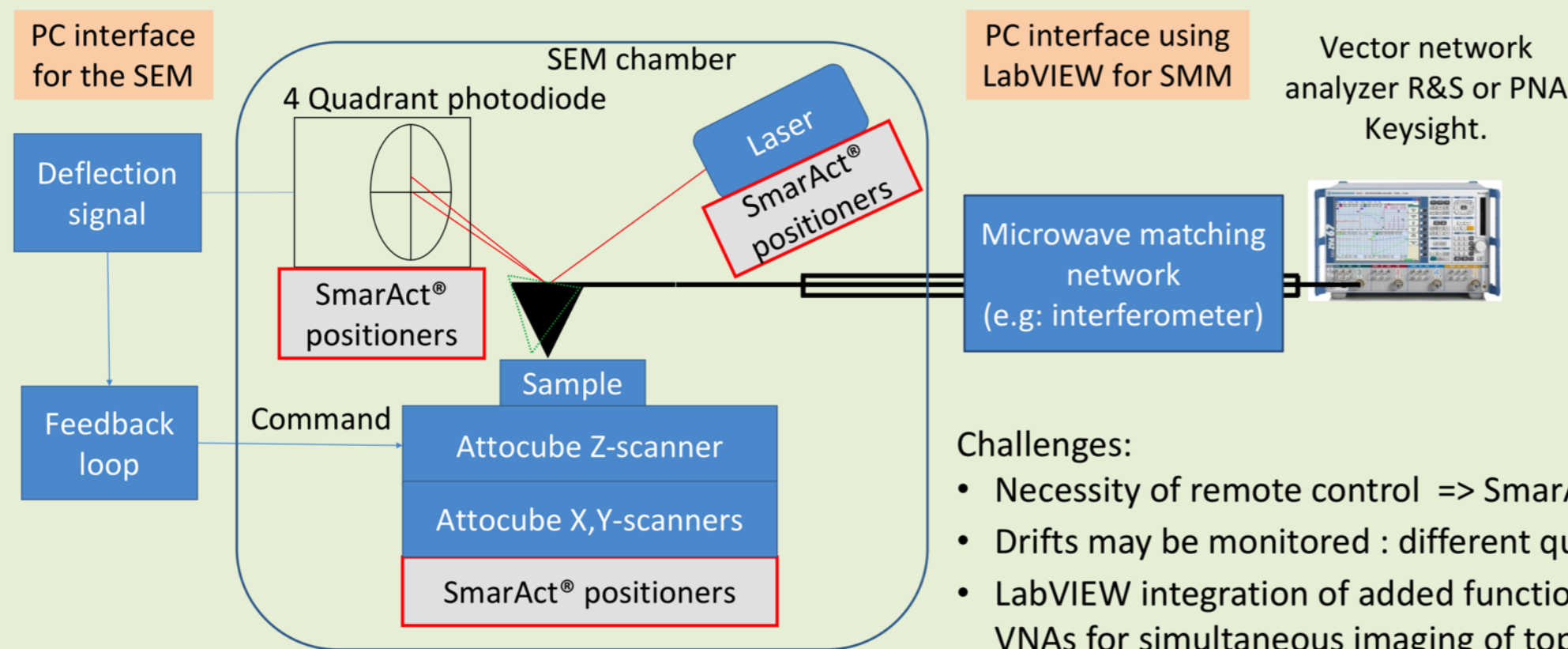
=> Proposed solution: combining SMM with SEM for monitoring humidity and tip degradation.

Complementary objective: development of Scanning Microwave Microscopy (SMM) technology towards high performance : spatial electrical resolution, increased frequency range (up to 110 GHz), and different sizes of microwave probes.

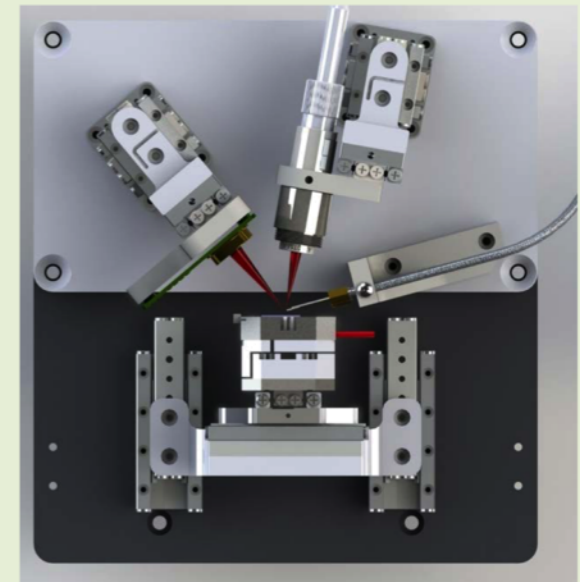


SMM in SEM instrumentation

Design of the mm-wave SMM compatible with the SEM chamber size and environment



SEMM platform implementation (SolidWorks®)

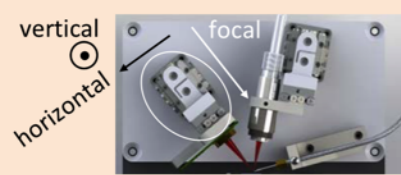
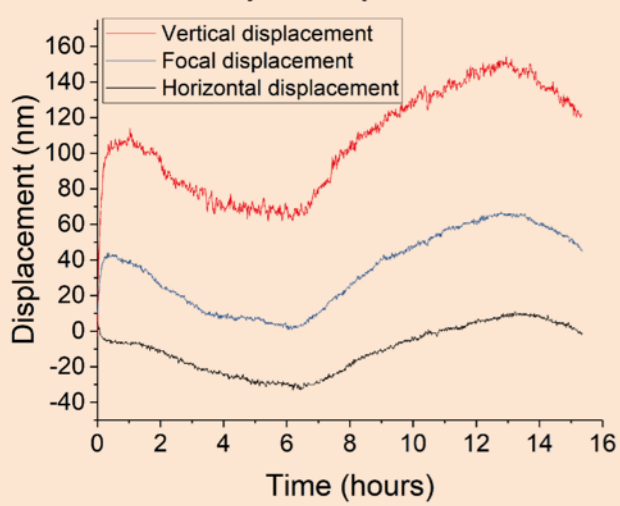


Challenges:

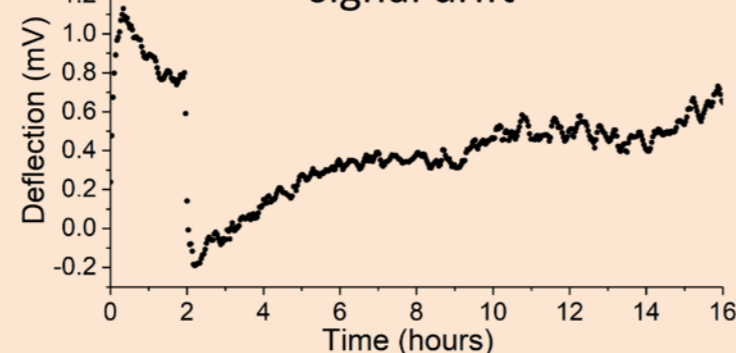
- Necessity of remote control => SmarAct® piezoelectric nano-positioners are included.
- Drifts may be monitored : different quantities are measured and analyzed.
- LabVIEW integration of added functionalities using Keysight® and Rohde&Schwarz® (R&S) VNAs for simultaneous imaging of topography (Nanonis® software) and microwave signals.

Instrument qualification

Drift of SmarAct® positioners detected by an optical sensor

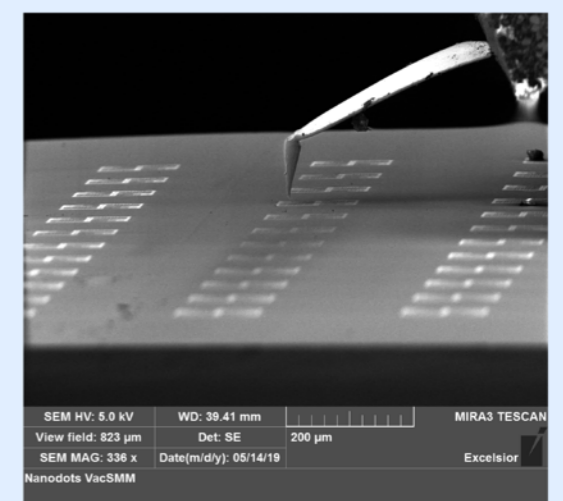
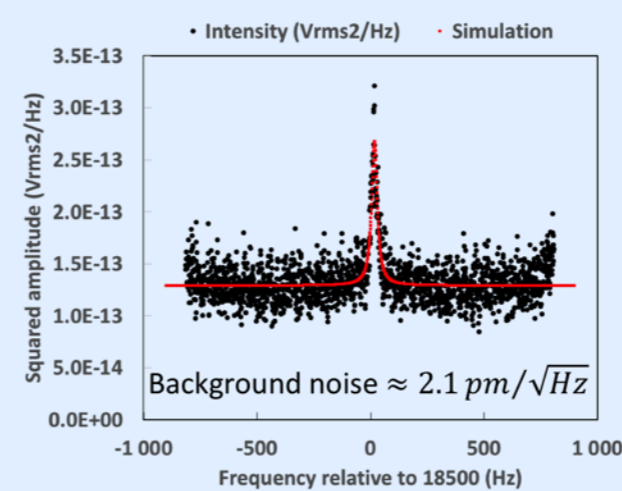


4Q photodiode deflection signal drift

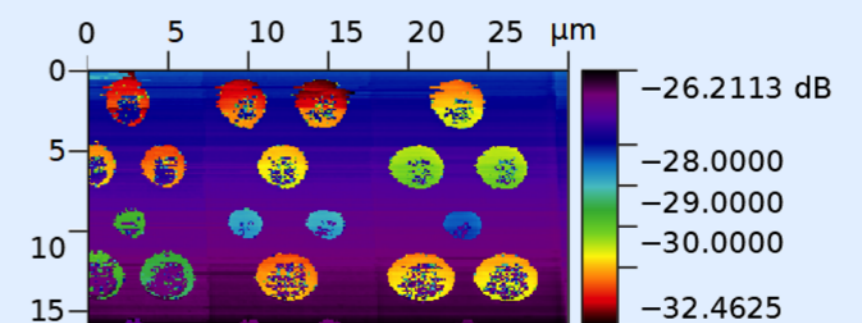
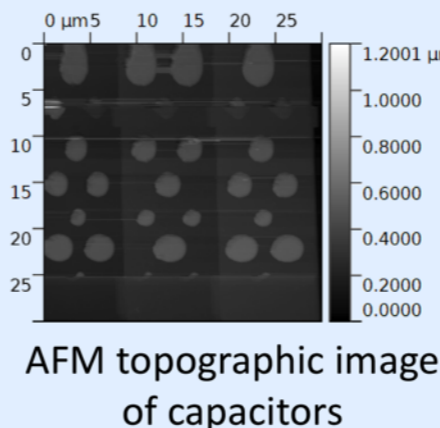


- 4 quadrant diode position stable within a 100 nm range over 16 hours => much lower than the spot size (~ a few µm) and position on the cantilever (10s of nm).
- Deflection signal stability of 1 mV <=> 10 nm fluctuation.

SMM and SEM results



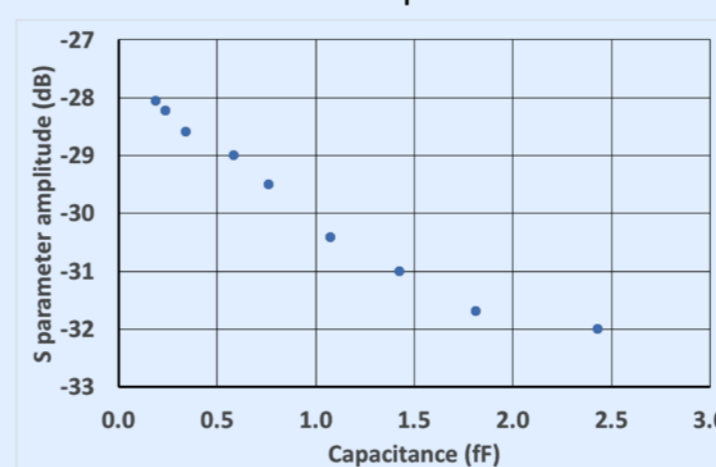
- Thermomechanical noise detection of the cantilever (25Pt300D RMN®).
- SEM observation of a capacitance calibration sample and AFM probe.



Amplitude of the microwave reflection coefficient (S parameter)

Dependence of the S parameter with the capacitance value => possible calibration of the microwave signal for further impedance measurement.

- Frequency = 7.59 GHz
- Microwave signal power = -5 dBm
- Demodulation IF Bandwidth = 100 Hz

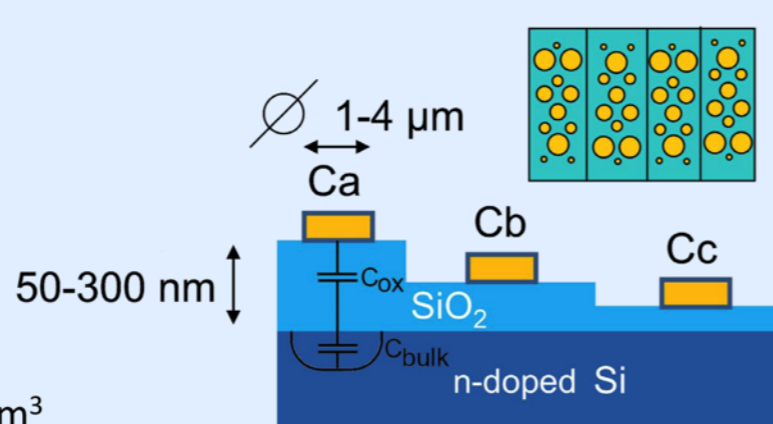


$$C_{ox} = A \frac{\epsilon_0 \epsilon_r \text{SiO}_2}{d_{ox}}$$

$$C_{depl} = A \frac{\epsilon_0 \epsilon_r \text{Si}}{d_{depl}}$$

$$d_{depl} = \sqrt{2 \epsilon_0 \epsilon_r \text{Si} \psi / q N_A}$$

$$\psi = 200 \text{ mV} \quad N_A = 8 \times 10^{15} / \text{cm}^3$$



Calibration sample :

- Si wafer with SiO₂ staircase and Au disks as top electrodes (1 to 4 µm ø).
- Capacitance modeling : oxide and depletion capacitances in series

Acknowledgements: The authors would like to thank C. Boyaval and C. Brillard for their technical contribution to the SEMM design and setup. This work has received funding from the European Union H2020 Programme (NMBP-07-2017) under grant agreement n°761036 MMAMA and from the ANR program Equipex (ExCELSiOR).